

SMD Schottky Barrier Diode

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CDBU00340 (Lead-free Device)

$I_o = 30 \text{ mA}$

$V_R = 40 \text{ Volts}$



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low capacitance.

Majority carrier conduction.

Mechanical data

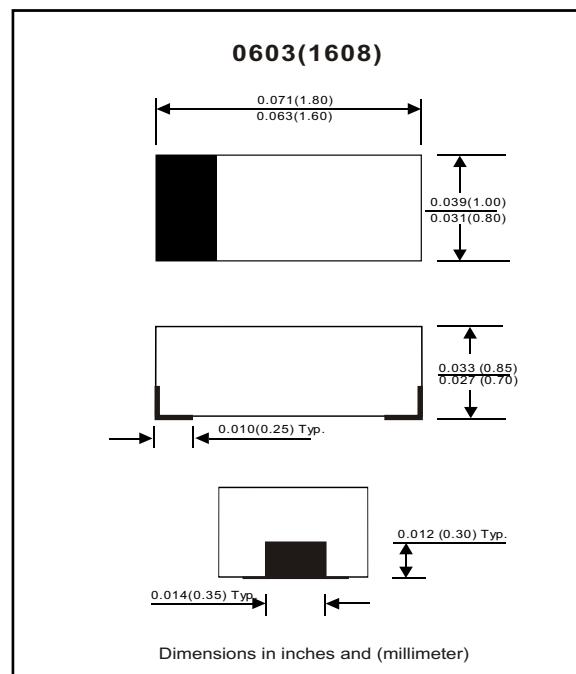
Case: 0603 (1608) Standard package , molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.003 gram (approximately).



Maximum Rating (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			45	V
Reverse voltage		V_R			40	V
Average forward current		I_o			30	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}		500		mA
Power Dissipation		P_D			150	mW
Storage temperature		T_{STG}	-40		+125	$^\circ\text{C}$
Junction temperature		T_j	-40		+125	$^\circ\text{C}$

Electrical Characteristics (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 1 \text{ mA DC}$	V_F			0.37	V
Reverse current	$V_R = 30 \text{ V}$ $V_R = 40 \text{ V}$	I_R			0.5 1	uA
Capacitance between terminals	$f = 1 \text{ MHz}$, and 1 VDC reverse voltage	C_T		1.5		pF

RATING AND CHARACTERISTIC CURVES (CDBU00340)

Fig. 1 - Forward characteristics

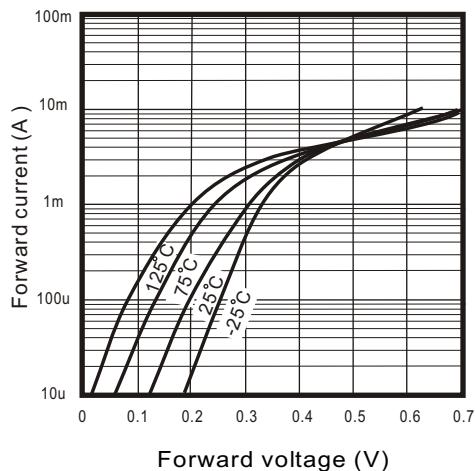


Fig. 2 - Reverse characteristics

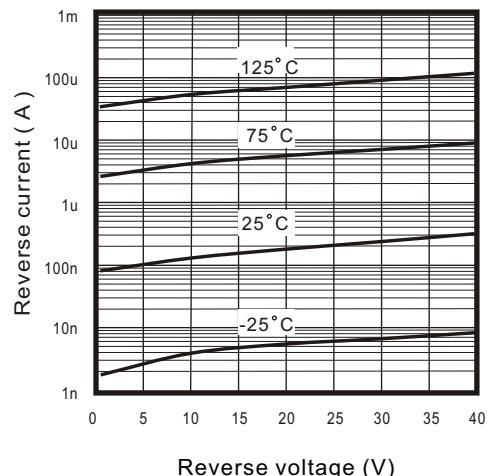


Fig. 3 - Capacitance between terminals characteristics

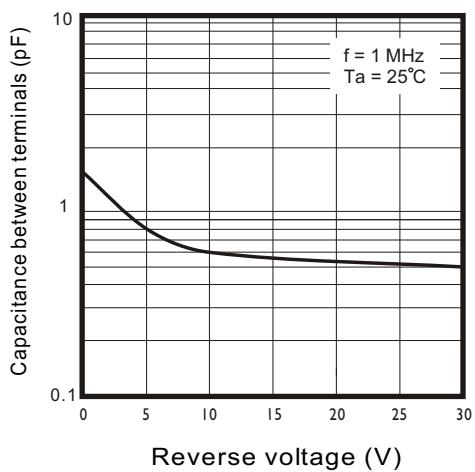


Fig. 4 - Current derating curve

